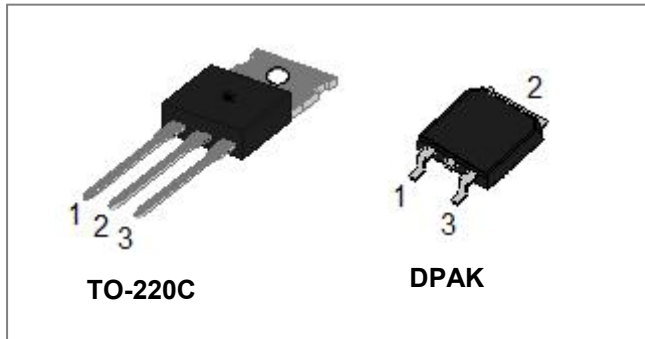
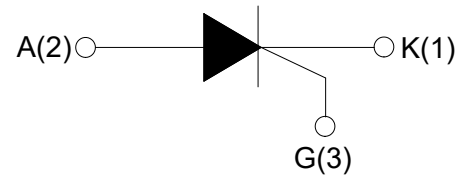


SCT151 Series 12A SCRs



Circuit Diagram



Description

With high ability to withstand the shock loading of large current, SCT151 series of silicon controlled rectifiers provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Storage junction temperature range	T_{stg}	-	-40-150	°C
Operating junction temperature range	T_j	-	-40-125	°C
Repetitive peak off-state voltage($T_j=25^{\circ}\text{C}$)	V_{DRM}	-	650/800	V
Repetitive peak reverse voltage($T_j=25^{\circ}\text{C}$)	V_{RRM}	-	650/800	V
RMS on-state current	$I_{(TRMS)}$	DPAK($T_c=98^{\circ}\text{C}$)	12	A
		TO-220C($T_c=100^{\circ}\text{C}$)		
Non repetitive surge peak on-state current ($t_p=10\text{ms}$)	I_{TSM}	-	120	A
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	-	72	A^2s
Repetitive rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di_T/dt	-	50	$\text{A}/\mu\text{s}$
Peak gate current	I_{GM}	-	2	A
Peak gate power	P_{GM}	-	5	W
Average gate power dissipation	$P_{G(AV)}$	-	0.5	W

Electrical Characteristics (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I _{GT}	V _D =12V R _L =33Ω	-	4	15	mA
V _{GT}		-	0.75	1.5	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	0.2	-	-	V
I _L	I _G =1.2I _{GT}	-	12	40	mA
I _H	I _T =500mA	-	12	30	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125°C	200	400	-	V/μs

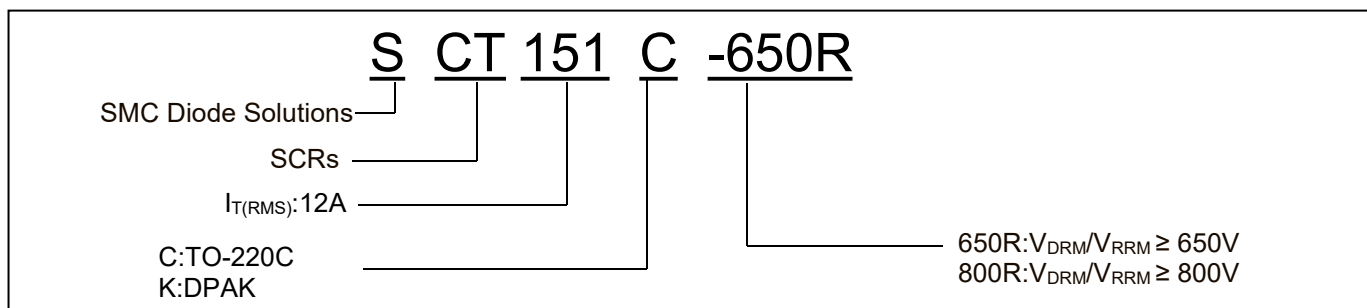
Static Characteristics

Symbol	Condition	Max.	Units
V _{TM}	I _T =23A t _p =380μs, T _j =25°C	1.6	V
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM} , T _j =25°C	10	μA
I _{RRM}	V _D =V _{DRM} V _R =V _{RRM} , T _j =125°C	1	mA

Thermal Resistances

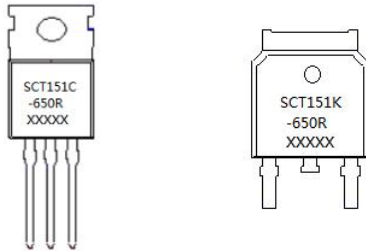
Symbol	Condition	Value	Units
R _{th(j-c)}	Junction to case(AC)	DPAK	1.4
		TO-220C	1.3

Ordering Information



Device	Package	Shipping
SCT151C-650R	TO-220C	50pcs/ Tube
SCT151K -650R/800R	DPAK	2500pcs/ Reel
SCT151K -650R/800RTR	DPAK	2500pcs/ Reel

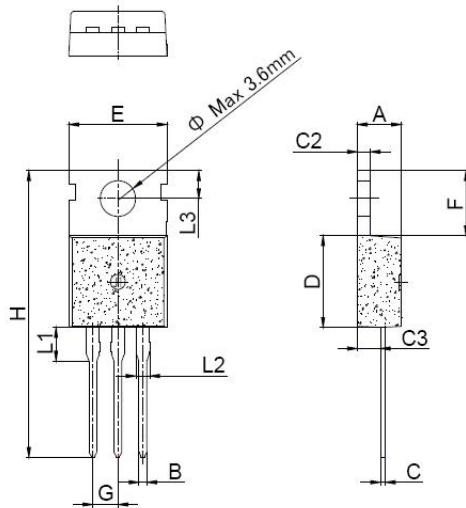
Marking Diagram



Where XXXXX is YYWWL

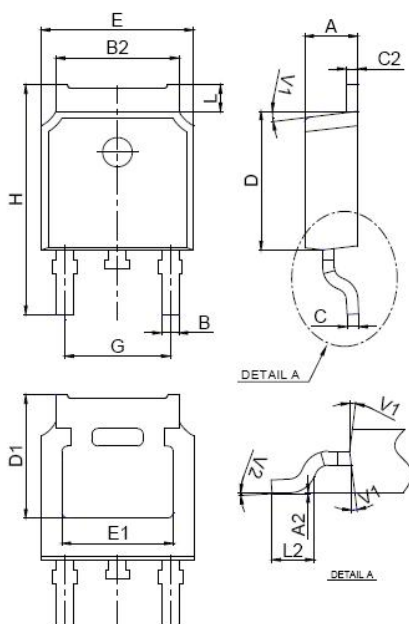
SCT151C-650R = Part name
SCT151K-650R = Part name
YY = Year
WW = Week
L = Lot Number

Mechanical Dimensions TO-220C



SYMBOL	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.39		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
φ		3.6			0.142	

Mechanical Dimensions DPAK



SYMBOL	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1	7°			7°		
V2	0°		6°	0°		6°

Ratings and Characteristics Curves

FIG.1: Maximum power dissipation versus RMS on-state current

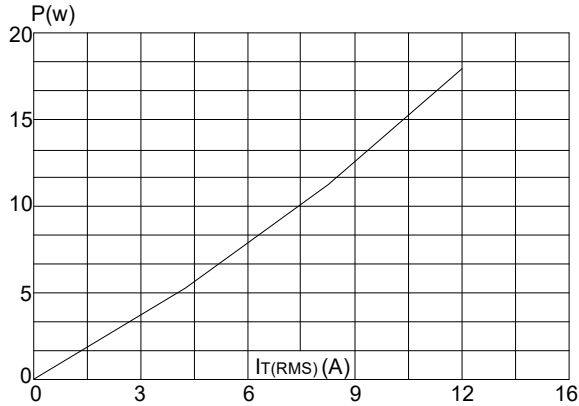


FIG.3: Surge peak on-state current versus number of cycles

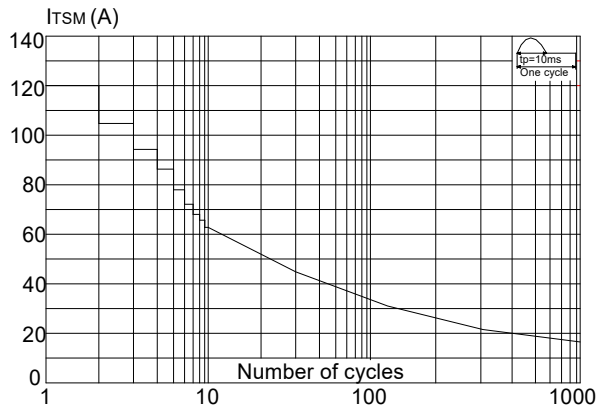


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $\int i^2 t$ ($di/dt < 50\text{A}/\mu\text{s}$)

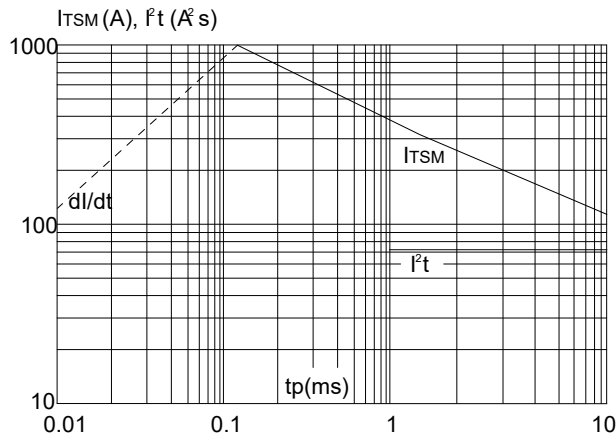


FIG.2: RMS on-state current versus case temperature

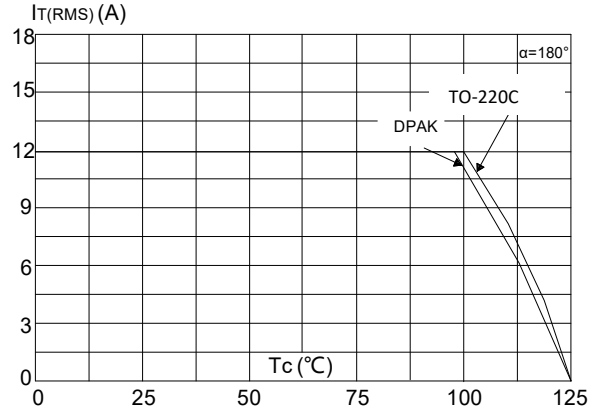


FIG.4: On-state characteristics (maximum values)

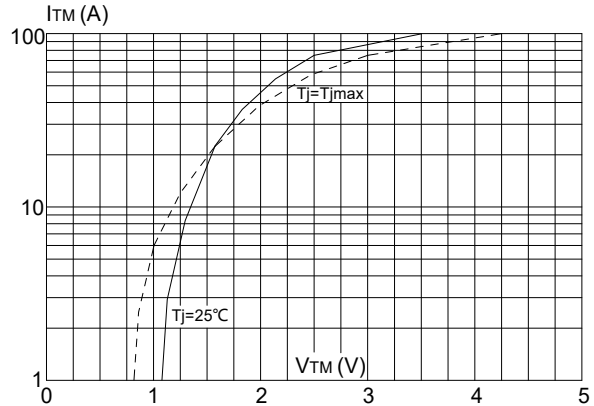
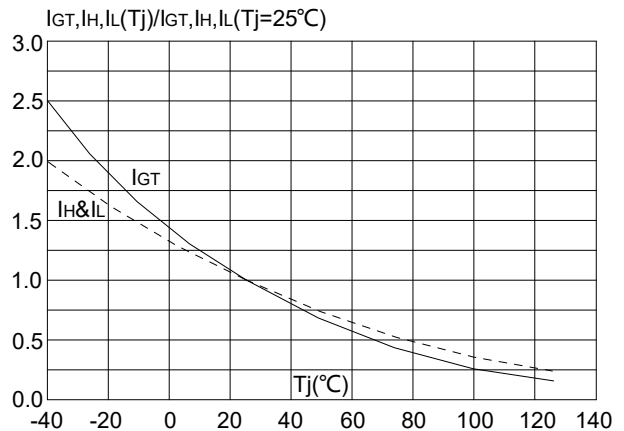


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



Technical Data
Data Sheet N2049, Rev.-



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